TriQuint SEMICONDUCTOR

Advance Product Information

Wideband Driver Amplifier

TGA8399C-EPU

Key Features and Performance

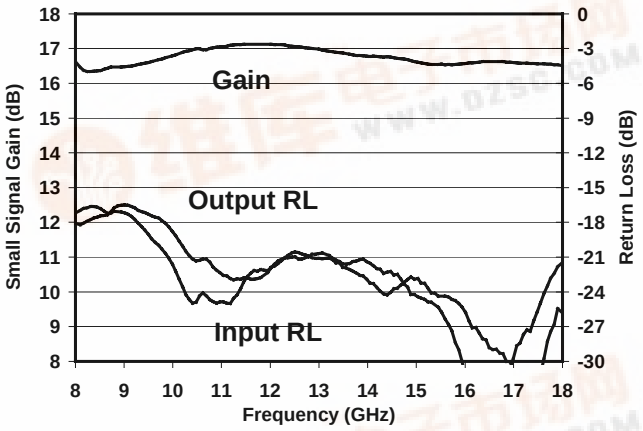
- Two Stage Driver Amplifier
- 0.25um pHEMT Technology
- 8-18 GHz Frequency Range
- 13 dBm Nominal Pout
- 17 dB Nominal Gain
- Balanced In/Out for Low VSWR
- 4.5V @ 50mA Self Bias

Primary Applications

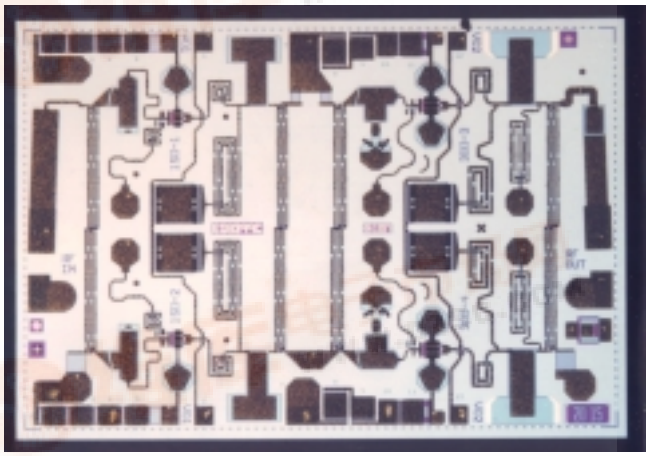
- X and Ku band Driver
- Point-to-Point Radio

Release Status

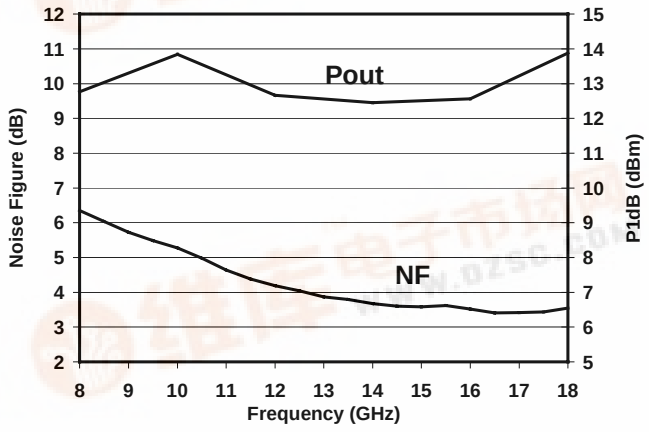
- Engineering Prototype Unit (EPU)



Typical Measured Small Signal Gain & RL



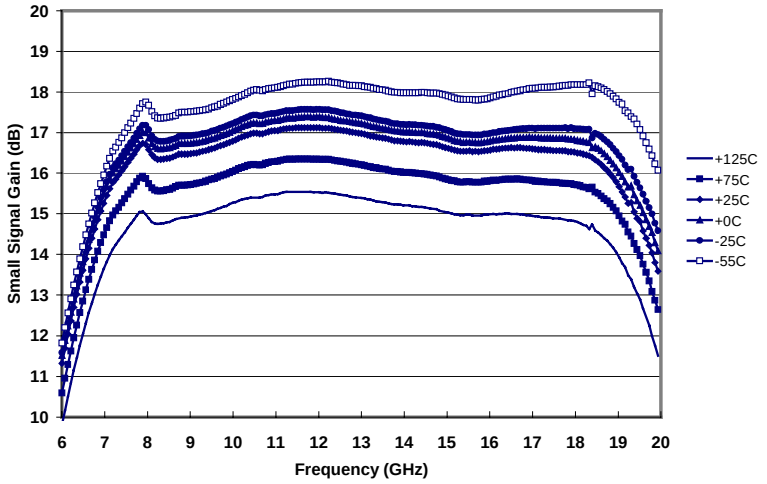
Chip Dimensions 3.5mm x2.4mm x 0.152mm

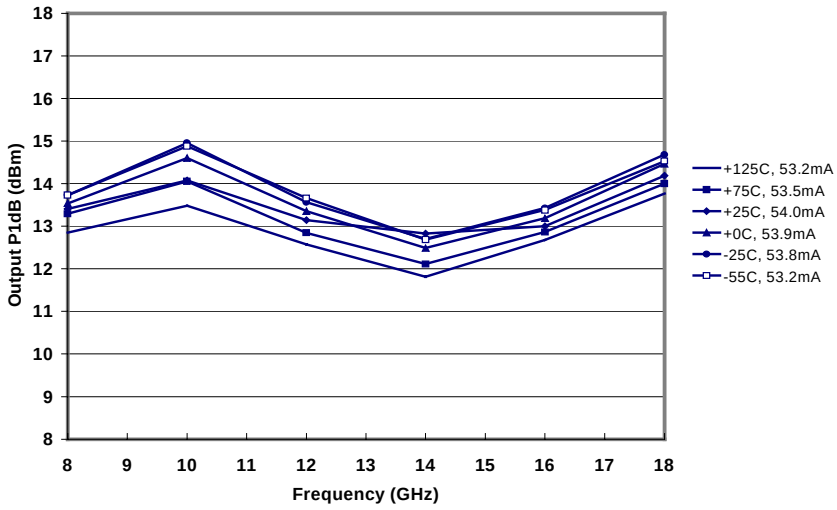


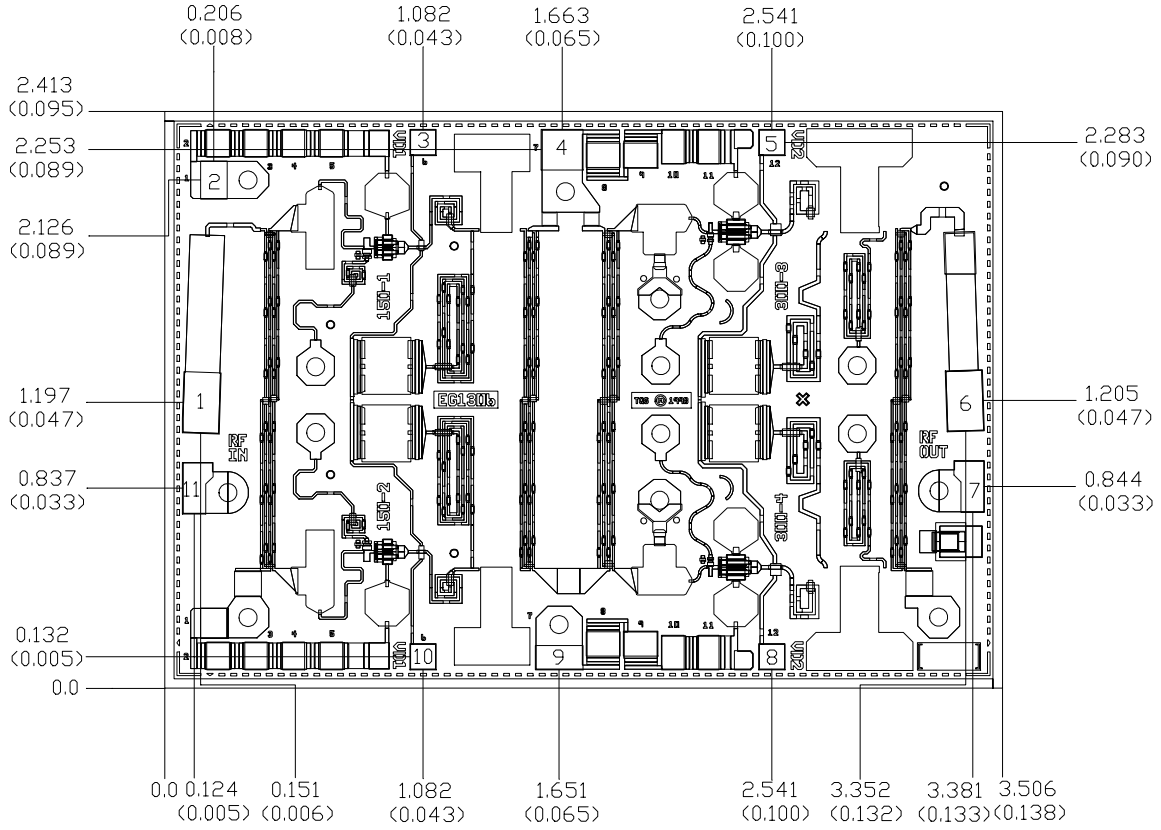
Typical Measured Pout and NF

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications.

TGA8399C Performance vs Temperature







Units: millimeters (inches)
Thickness: 0.1524 (0.006) (reference only)
Chip edge to bond pad dimensions are shown to center of bond pad
Chip size tolerance: +/- 0.051 (0.002)

Bond Pad #1 (RF Input)	0.155 x 0.255 (0.006 x 0.010)
Bond Pad #2 (GND)	0.111 x 0.160 (0.004 x 0.006)
Bond Pad #3,#10 (VD1)	0.110 x 0.110 (0.004 x 0.004)
Bond Pad #4 (GND)	0.170 x 0.175 (0.007 x 0.007)
Bond Pad #5,#8 (VD2)	0.110 x 0.110 (0.004 x 0.004)
Bond Pad #6 (RF Output)	0.155 x 0.255 (0.006 x 0.010)
Bond Pad #7,#11 (GND)	0.098 x 0.217 (0.004 x 0.009)
Bond Pad #9 (GND)	0.102 x 0.200 (0.004 x 0.008)

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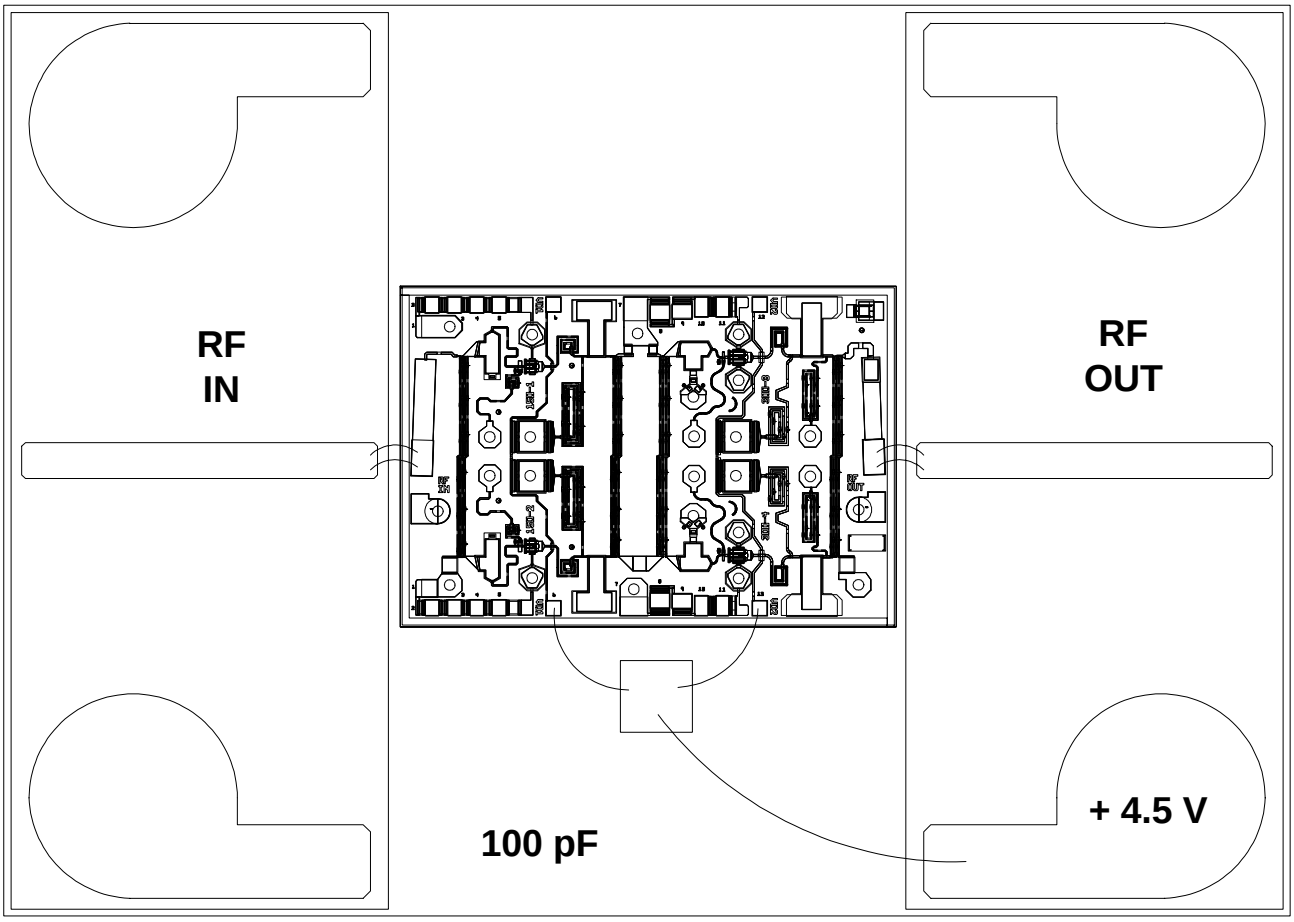
Recommended Assembly Layout



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